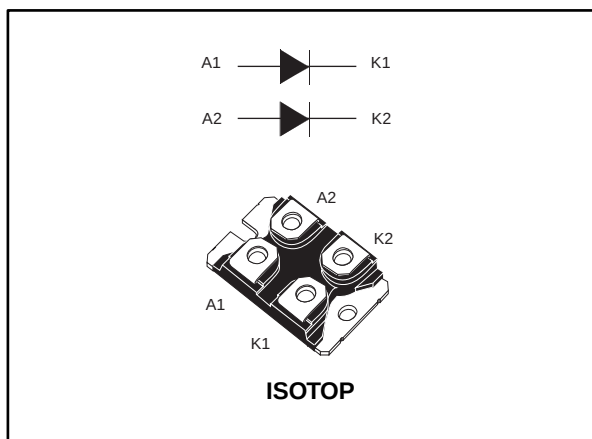


Turbo 2 ultrafast high voltage rectifier

Datasheet - production data



Description

This device that uses ST Turbo 2 600 V technology, is specially suited for use in switching power supplies, and industrial applications, as rectification and freewheeling diode.

Table 1: Device summary

Symbol	Value
$I_{F(AV)}$	2 x 60 A
V_{RRM}	600 V
T_j (max.)	150 °C
V_F (typ.)	0.95 V
t_{rr} (max.)	70 ns

Features

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching and conduction losses
- Insulated package ISOTOP:
 - Insulated voltage: 2500 V_{RMS} sine



TM: ISOTOP is a trademark of STMicroelectronics

1 Characteristics

Table 2: Absolute ratings (limiting values, per diode)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		600	V
$I_{F(RMS)}$	Forward rms current		120	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$	$T_C = 65\text{ }^{\circ}\text{C}$, per diode	60	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal	500	A
T_{stg}	Storage temperature range		-55 to +150	$^{\circ}\text{C}$
T_j	Maximum operating junction temperature		150	$^{\circ}\text{C}$

Table 3: Thermal parameters

Symbol	Parameter		Maximum values	Unit
$R_{th(j-c)}$	Junction to case	Per diode	0.98	$^{\circ}\text{C/W}$
		Total	0.54	
$R_{th(c)}$	Coupling		0.1	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode1}) = P_{(\text{diode1})} \times R_{th(j-c)} (\text{per diode}) + P_{(\text{diode2})} \times R_{th(c)}$$

Table 4: Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ }^{\circ}\text{C}$	$V_R = V_{RRM}$	-		50	μA
		$T_j = 125\text{ }^{\circ}\text{C}$		-	50	500	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ }^{\circ}\text{C}$	$I_F = 60\text{ A}$	-		1.55	V
		$T_j = 150\text{ }^{\circ}\text{C}$		-	0.95	1.20	

Notes:

⁽¹⁾Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$

⁽²⁾Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses, use the following equation:

$$P = 0.93 \times I_{F(AV)} + 0.0045 \times I_{F(RMS)}^2$$

Table 5: Dynamic characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$T_J = 25^\circ\text{C}$	$I_F = 0.5\text{ A}, I_{rr} = 0.25\text{ A}, I_R = 1\text{ A}$	-		70	ns
			$I_F = 1\text{ A}, di_F/dt = 50\text{ A}/\mu\text{s}, V_R = 30\text{ V}$	-	75	105	
I_{RM}	Reverse recovery current	$T_J = 125^\circ\text{C}$	$I_F = 60\text{ A}, di_F/dt = 400\text{ A}/\mu\text{s}, di_F/dt = 100\text{ A}/\mu\text{s}$	-	14	19	A
t_{fr}	Forward recovery time	$T_J = 25^\circ\text{C}$	$I_F = 60\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$	-		500	ns
V_{FP}	Forward recovery voltage	$T_J = 25^\circ\text{C}$	$I_F = 60\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$	-	3		V

1.1 Characteristics (curves)

Figure 1: Conduction losses versus average forward current (per diode)

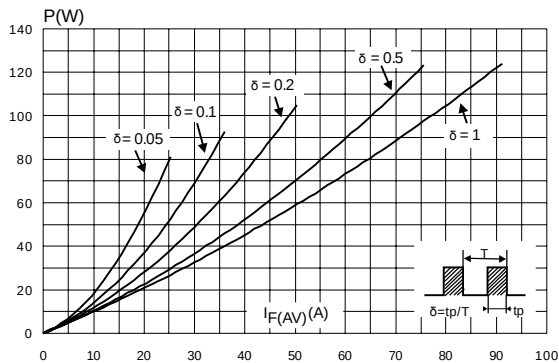


Figure 2: Forward voltage drop versus forward current (per diode)

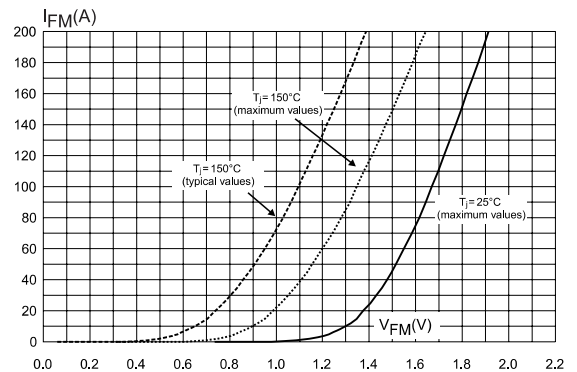


Figure 3: Relative variation of thermal impedance junction to case versus pulse duration

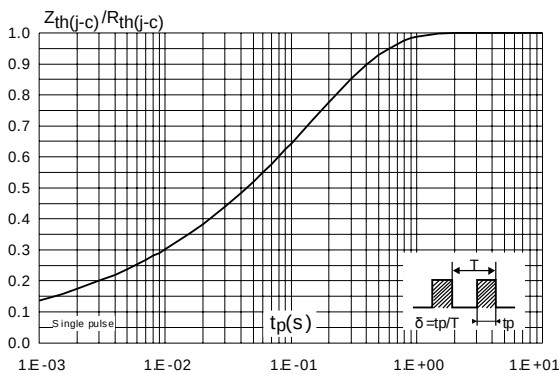


Figure 4: Peak reverse recovery current versus dI_F/dt (typical values, per diode)

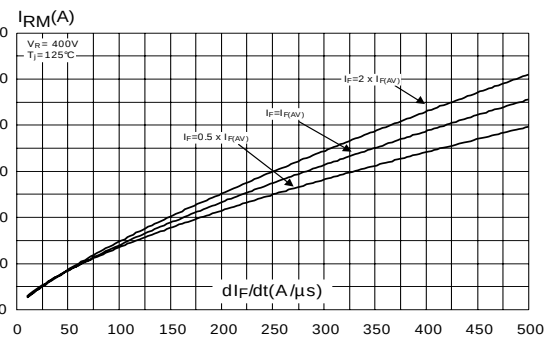


Figure 5: Reverse recovery time versus dI_F/dt (typical values, per diode)

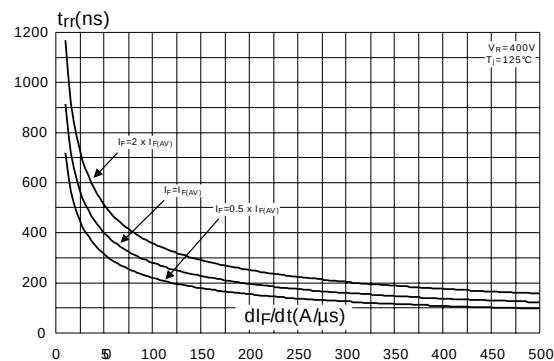


Figure 6: Reverse recovery charges versus dI_F/dt (typical values, per diode)

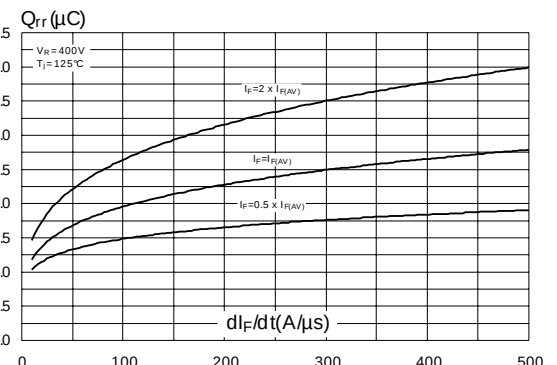


Figure 7: Reverse recovery softness factor versus dI_F/dt (typical values, per diode)

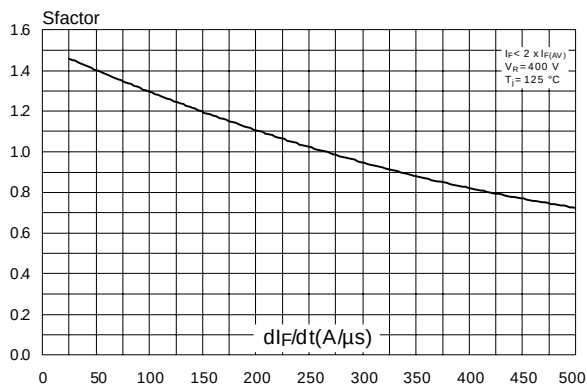


Figure 8: Relative variations of dynamic parameters versus junction temperature

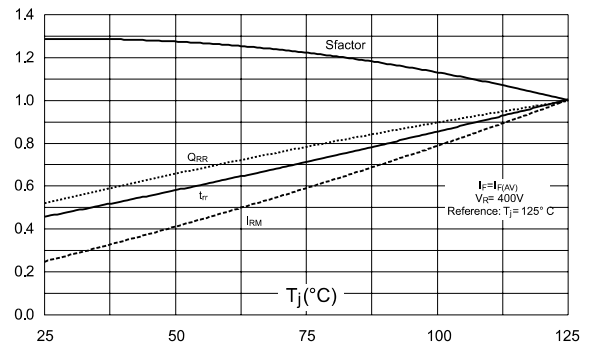


Figure 9: Transient peak forward voltage versus dI_F/dt (typical values, per diode)

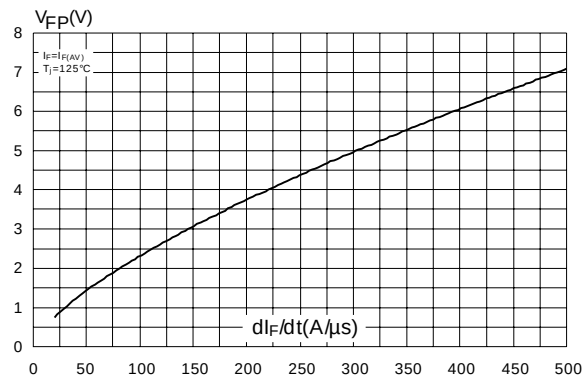


Figure 10: Forward recovery time versus dI_F/dt (typical values, per diode)

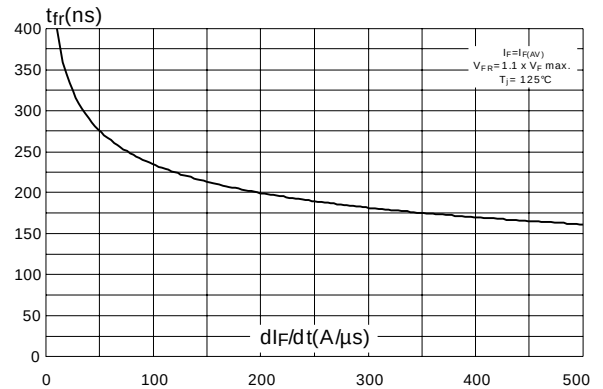
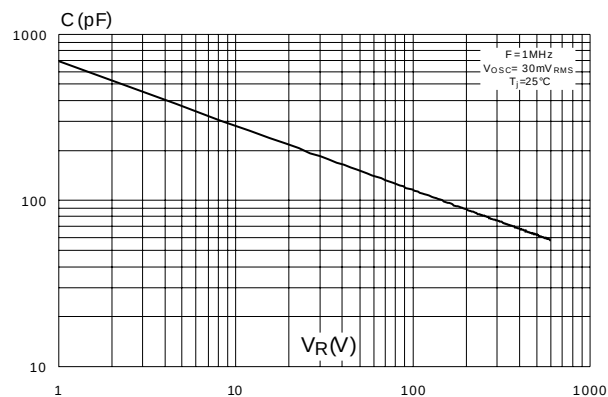


Figure 11: Junction capacitance versus reverse voltage applied (typical values, per diode)



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 1.3 N·m
- Maximum torque value: 1.5 N·m

STMicroelectronics strongly recommends the use of the screws delivered with this product.

The use of any other screws is entirely at the user's own risk and will invalidate the warranty.

2.1 ISOTOP package information

Figure 12: ISOTOP package outline

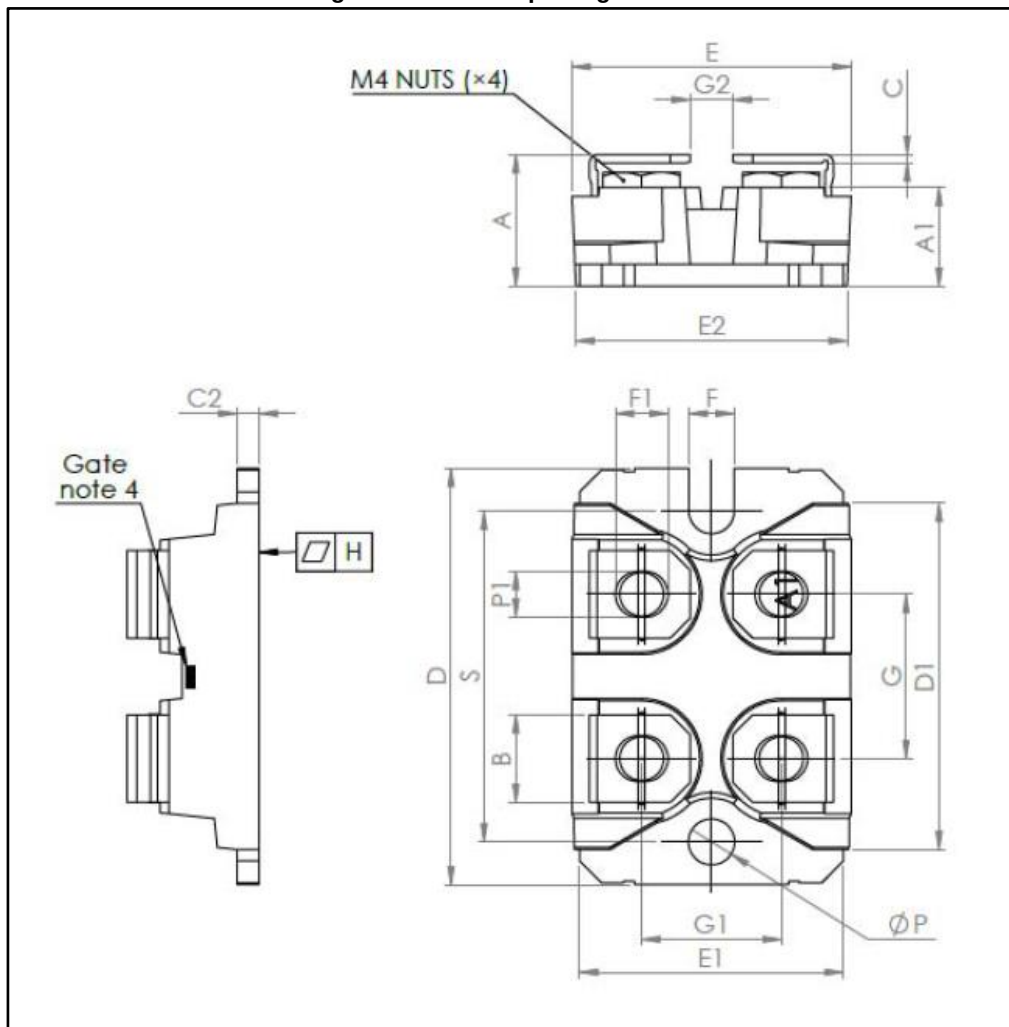


Table 6: ISOTOP package mechanical data

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.460	0.480
A1	8.90	9.10	0.350	0.358
B	7.80	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80		0.976	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5	0.181	0.197
H	-0.05	0.1	-0.002	0.004
Diam P	4	4.30	0.157	0.169
P1	4	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

3 Ordering information

Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STTH120L06TV1	STTH120L06TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
07-Sep-2004	1	First issue.
04-Apr-2011	2	Updated <i>Chapter 2: Package information..</i>
20-Jan-2017	3	Updated section "Features" and section 2.2: "ISOTOP package information".
22-Jan-2018	4	Added cote "H" (-0.05 mm min - 0.1mm max in ISOTOP package information.

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9